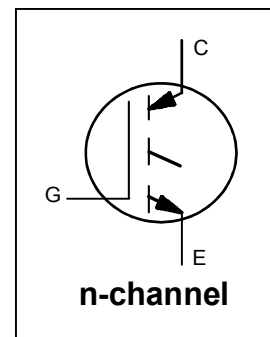


$V_{CES} = 1200V$   
 $I_{C(Nominal)} = 75A$   
 $T_{J(max)} = 175^{\circ}C$   
 $V_{CE(on)} typ = 1.9V @ I_C = 75A$



**Applications**

- Medium Power Drives
- UPS
- HEV Inverter
- Welding
- Induction Heating

<b>G</b>	<b>C</b>	<b>E</b>
Gate	Collector	Emitter

Features	Benefits
Low $V_{CE(ON)}$ and switching Losses	High efficiency in a wide range of applications and switching frequencies
Square RBSOA and Maximum Junction Temperature $175^{\circ}C$	Improved Reliability due to rugged hard switching performance and higher power capability
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent current sharing in parallel operation

Base part number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRG7CH73K10EF	Die on Film	Wafer	1	IRG7CH73K10EF

**Mechanical Parameter**

Die Size	9.07 x 9.07	mm <sup>2</sup>
Minimum Street Width	75	μm
Emitter Pad Size (Included Gate Pad)	See Die Drawing	mm <sup>2</sup>
Gate Pad Size	1.11 x 1.10	
Area Total / Active	82.26/ 59.1	
Thickness	140	μm
Wafer Size	200	mm
Notch Position	0	Degrees
Maximum-Possible Chips per Wafer	312 pcs.	
Passivation Front side	Silicon Nitride	
Front Metal	Al, Si (4μm)	
Backside Metal	Al (0.1μm), Ti (0.1μm), Ni (0.4μm), Ag (0.6μm)	
Die Bond	Electrically conductive epoxy or solder	
Reject Ink Dot Size	0.25 mm diameter minimum	

**Maximum Ratings**

	Parameter	Max.	Units
$V_{CE}$	Collector-Emitter Voltage, $T_J=25^\circ\text{C}$	1200	V
$I_C$	DC Collector Current	①	A
$I_{LM}$	Clamped Inductive Load Current ④	300	A
$V_{GE}$	Gate Emitter Voltage	$\pm 30$	V
$T_J, T_{STG}$	Operating Junction and Storage Temperature	-40 to +175	$^\circ\text{C}$

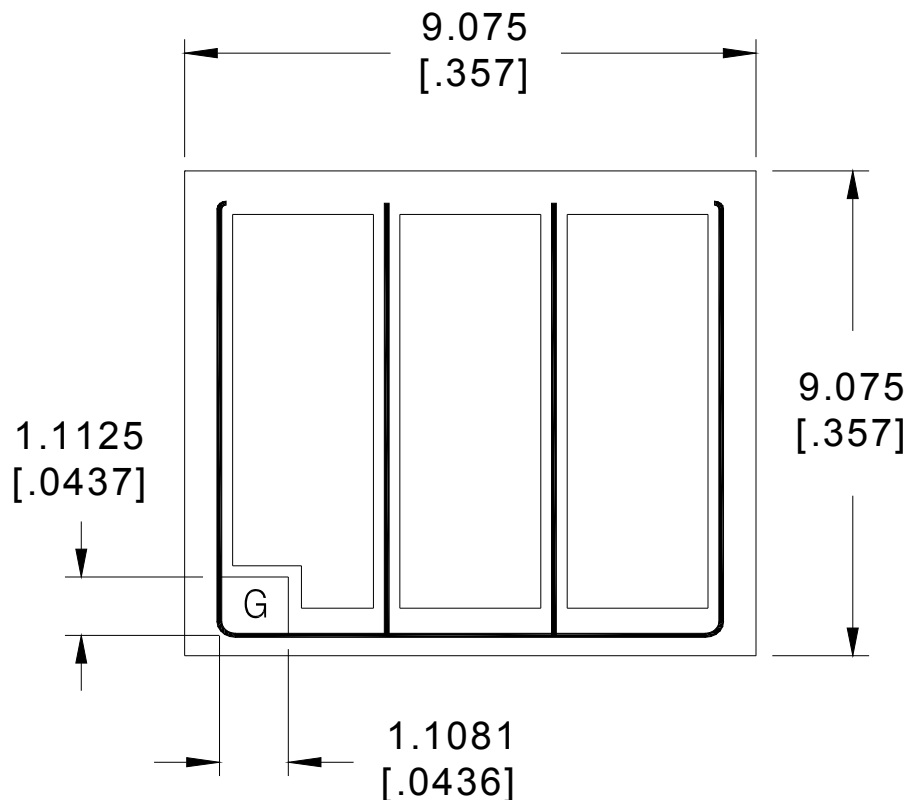
**Static Characteristics (Tested on wafers) .  $T_J=25^\circ\text{C}$** 

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0\text{V}, I_C = 250\mu\text{A}$ ⑤
$V_{CE(sat)}$	Collector-to-Emitter Saturated Voltage	—	1.4	1.6	V	$V_{GE} = 15\text{V}, I_C = 20\text{A}, T_J = 25^\circ\text{C}$
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	5.0	—	7.5		$I_C = 3.5\text{mA}, V_{GE} = V_{CE}$
$I_{CES}$	Zero Gate Voltage Collector Current	—	1.0	25		$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}$
$I_{GES}$	Gate Emitter Leakage Current	—	—	$\pm 400$	nA	$V_{CE} = 0\text{V}, V_{GE} = \pm 30\text{V}$

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{CE(sat)}$	Collector-to-Emitter Saturated Voltage	—	1.9	2.3	V	$V_{GE} = 15\text{V}, I_C = 75\text{A}, T_J = 25^\circ\text{C}$
		—	2.5	—		$V_{GE} = 15\text{V}, I_C = 75\text{A}, T_J = 175^\circ\text{C}$
SCSOA	Short Circuit Safe Operating Area	10	—	—	$\mu\text{s}$	$V_{GE}=15\text{V}, V_{CC}=600\text{V},$ ② $R_G=4.7\Omega, V_P \leq 1200\text{V}, T_J=150^\circ\text{C}$
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 300\text{A}$ $V_{CC} = 960\text{V}, V_P \leq 1200\text{V}$ $R_g = 4.7\Omega, V_{GE} = +20\text{V to } 0\text{V}$
$C_{iss}$	Input Capacitance	—	9450	—	pF	$V_{GE} = 0\text{V}$
$C_{oss}$	Output Capacitance	—	340	—		$V_{CE} = 30\text{V}$
$C_{rss}$	Reverse Transfer Capacitance	—	230	—		$f = 1.0\text{MHz}$
$Q_g$	Total Gate Charge (turn-on)	—	360	—	nC	$I_C = 75\text{A}$ ⑥
$Q_{ge}$	Gate-to-Emitter Charge (turn-on)	—	87	—		$V_{GE} = 15\text{V}$
$Q_{gc}$	Gate-to-Collector Charge (turn-on)	—	180	—		$V_{CC} = 600\text{V}$

	Parameter	Min.	Typ.	Max.	Units	Conditions ③
$t_{d(on)}$	Turn-On delay time	—	63	—	ns	$I_C = 75\text{A}, V_{CC} = 600\text{V}$ $R_G = 4.7\Omega, V_{GE}=15\text{V}, L=200\mu\text{H}$ $T_J = 25^\circ\text{C}$
$t_r$	Rise time	—	118	—		
$t_{d(off)}$	Turn-Off delay time	—	267	—		
$t_f$	Fall time	—	114	—		
$t_{d(on)}$	Turn-On delay time	—	62	—		$I_C = 75\text{A}, V_{CC} = 600\text{V}$ $R_G = 4.7\Omega, V_{GE}=15\text{V}, L= 200\mu\text{H}$ $T_J = 175^\circ\text{C}$
$t_r$	Rise time	—	110	—		
$t_{d(off)}$	Turn-Off delay time	—	330	—		
$t_f$	Fall time	—	237	—		

# Die Drawing


**NOTES:**

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
2. CONTROLLING DIMENSION: [INCH].
3. LETTER DESIGNATION:  
S = SOURCE  
G = GATE
4. DIMENSIONAL TOLERANCES:  

BONDING PADS:	< 0.635 TOLERANCE = +/- 0.013
WIDTH	< [.0250] TOLERANCE = +/- [.0005]
&	> 0.635 TOLERANCE = +/- 0.025
LENGTH	> [.0250] TOLERANCE = +/- [.0010]
OVERALL DIE:	< 1.270 TOLERANCE = +/- 0.102
WIDTH	< [.050] TOLERANCE = +/- [.004]
&	> 1.270 TOLERANCE = +/- 0.203
LENGTH	> [.050] TOLERANCE = +/- [.008]
5. DIE THICKNESS = 0.100 [.0039] - 0.140 [.0055]

**Notes:**

- ① The current in the application is limited by  $T_{JMax}$  and the thermal properties of the assembly.
- ② Not subject to production test- Verified by design / characterization.
- ③ Values influenced by parasitic L and C in measurement.
- ④  $V_{CC} = 80\% (V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 200\mu H$ ,  $R_G = 4.7\Omega$ .
- ⑤ Refer to AN-1086 for guidelines for measuring  $V_{(BR)CES}$  safely
- ⑥ Die Level Characterization.

### Additional Testing and Screening

For Customers requiring product supplied as Known Good Die (KGD) or requiring specific die level testing, please contact your local IR Sales.

### Shipping

Sawn Wafer on Film. Please contact your local IR sales office for non– standard shipping options

### Handling

- Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
- Product must be handled only in a class 10,000 or better-designated clean room environment.
- Singulated die are not to be handled with tweezers. A vacuum wand with a non-metallic ESD protected tip should be used.

### Wafer/Die Storage

- Proper storage conditions are necessary to prevent product contamination and/or degradation after shipment.
- Note: To reduce the risk of contamination or degradation, it is recommended that product not being used in the assembly process be returned to their original containers and resealed with a vacuum seal process.
- Sawn wafers on a film frame are intended for immediate use and have a limited shelf life.

### Further Information

For further information please contact your local IR Sales office or email your enquiry to <http://die.irf.com>

Data and specifications subject to change without notice.  
This product has been designed and qualified for Industrial market.  
Qualification Standards can be found on IR's Web site.

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**IOR** Rectifier

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